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FDA032N08 N-Channel PowerTrench[®] MOSFET 75 V, 235 A, 3.2 m Ω

Features

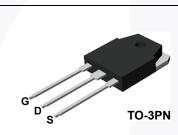
- $R_{DS(on)}$ = 2.5 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 75 A
- · Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{\text{DS}(\text{on})}$
- High Power and Current Handling Capability
- RoHS Compliant

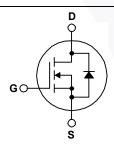
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench[®] process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		FDA032N08	Unit		
V _{DSS}	Drain to Source Voltage	75	V		
V _{GSS}	Gate to Source Voltage	±20	V		
ID		- Continuous (T _C = 25 ^o C, Silicon Limited)	235	A	
	Drain Current	- Continuous (T _C = 100°C, Silicon Limited)	165		
		- Continuous (T _C = 25 ^o C, Package Limited)	120		
I _{DM}	Drain Current	- Pulsed (Note 1)	940	A	
E _{AS}	Single Pulsed Avalanche Ener	rgy (Note 2)	1995	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		5.5	V/ns	
P _D	Dower Dissinction	$(T_{\rm C} = 25^{\rm o}{\rm C})$	375	W	
	Power Dissipation	- Derate Above 25°C	2.5	W/ºC	
T _J , T _{STG}	Operating and Storage Tempe	-55 to +175	°C		
TL	Maximum Lead Temperature 1	or Soldering, 1/8" from Case for 5 Seconds	300	°C	

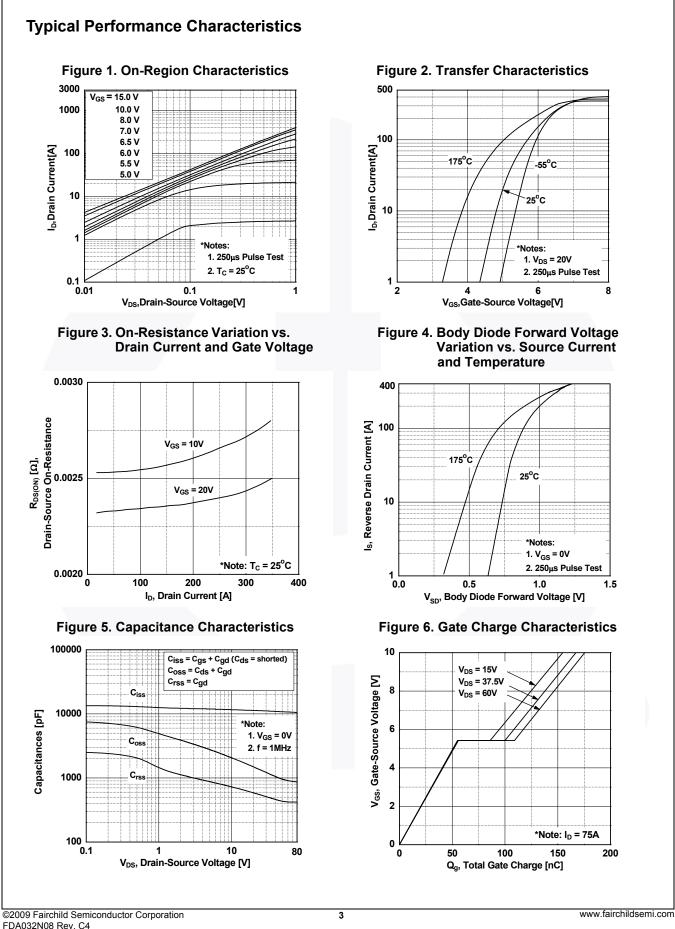
Thermal Characteristics

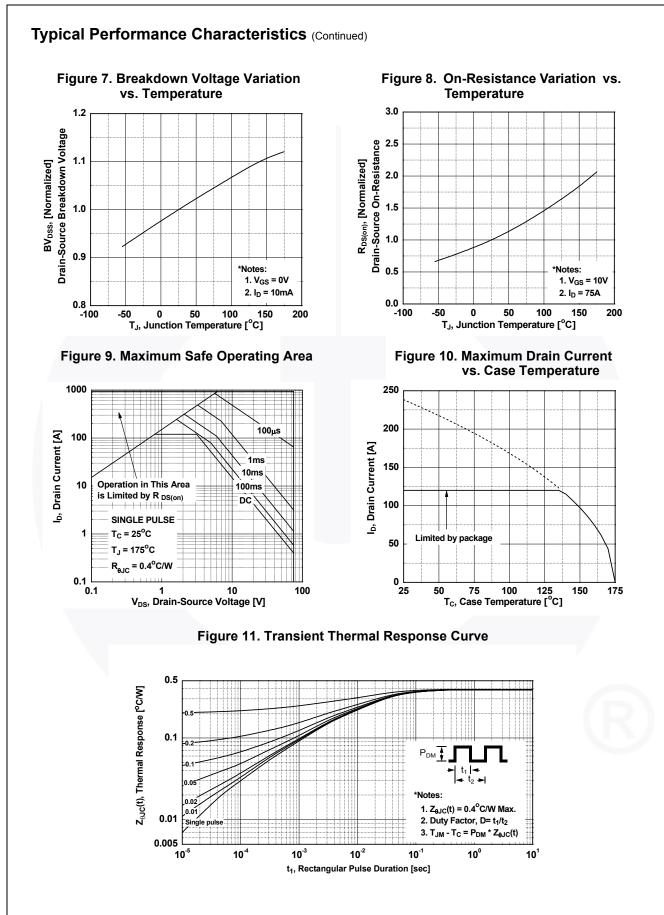
Symbol	Parameter	FDA032N08	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.4	°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max.	40	0/00

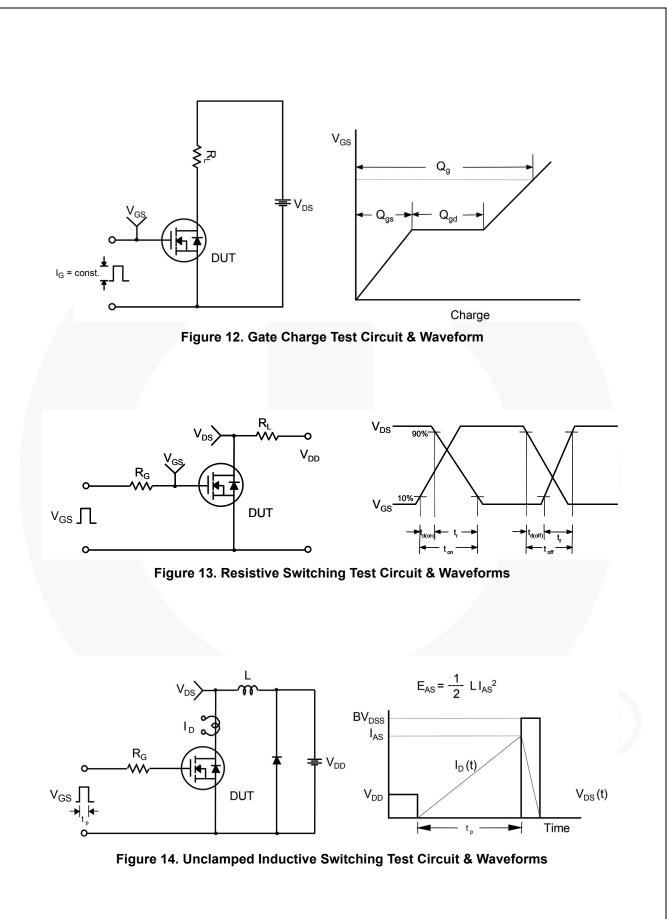
Part Nun	nber	Top Mark Pac		Packing Metho	d Reel Size	Тар	e Width	Qua	ntity
		FDA032N08	TO-3PN			N/A		30 units	
lectrica	l Char	racteristics T _C = 2	25°C unless	otherwise noted.					
Symbol		Parameter		Test Cond	itions	Min.	Тур.	Max.	Unit
off Charac	teristic	s							
BV _{DSS}	Drain to Source Breakdown Voltage		tage	I _D = 250 μA, V _{GS} = 0 V, T _C = 25 ^o C			_	_	V
BV _{DSS}	Breakdown Voltage Temperature		-			75			
$/\Delta T_J$	Coefficient		•	I_D = 250 µA, Referenced to 25°C			0.05	-	V/ºC
	Zero Gate Voltage Drain Current			V _{DS} = 75 V, V _{GS} = 0 V		-	-	1	•
DSS			It	$V_{DS} = 75 \text{ V}, \text{ T}_{C} = 150^{\circ}\text{C}$			-	500	μA
SSS	Gate to	Gate to Body Leakage Current		V_{GS} = ±20 V, V_{DS} =	0 V	-	-	±100	nA
n Charac	teristic	s							
GS(th)		hreshold Voltage		V _{GS} = V _{DS} , I _D = 250) IIA	2.5	3.5	4.5	V
DS(on)		Prain to Source On Resis	stance	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 75$		-	2.5	3.2	mΩ
FS		d Transconductance		$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 75$		-	180	-	S
ynamic C									
iss	-	apacitance	_				11400	15160	۳E
		Capacitance		V _{DS} = 25 V, V _{GS} = 0) V,		1360	1810	pF pF
oss		e Transfer Capacitance		f = 1 MHz			595	800	
rss		ate Charge at 10V	_		•	-	169	220	pF nC
g(tot)		Source Gate Charge		V _{DS} = 60 V, I _D = 75 V _{GS} = 10 V	А,		60	220	-
gs		Drain "Miller" Charge		V _{GS} - 10 V	(Note 4)	-	47	-	nC nC
gd		-			(-	47	-	
witching					1			1	
(on)		n Delay Time				-	230	470	ns
		Turn-On Rise Time		$V_{DD} = 37.5 \text{ V}, I_D = 75 \text{ A},$		-	191	392	ns
(off)	Turn-Of	f Delay Time		$R_{G} = 25 \Omega, V_{GS} = 10 V$		-	335	680	ns
	Turn-Of	f Fall Time			(Note 4)	-	121	252	ns
rain-Soui	rce Dio	de Characteristics							
	Maximu	Maximum Continuous Drain to Source Diode Forward Current					-	235	Α
M	Maximu	Maximum Pulsed Drain to Source Diode Forward Current				-	-	940	Α
SD	Drain to	Source Diode Forward	Voltage	V _{GS} = 0 V, I _{SD} = 75 A		-	-	1.3	V
	Reverse	e Recovery Time		$V_{GS} = 0 V, I_{SD} = 75 A,$ $dI_F/dt = 100 A/\mu s$		-	53	- /	ns
rr	Reverse	e Recovery Charge				-	77	/ -	nC

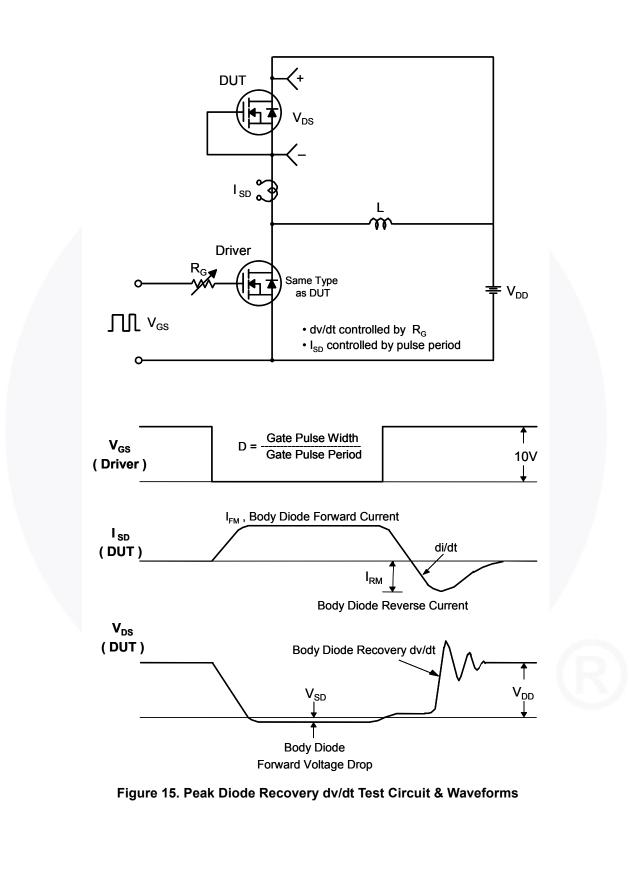
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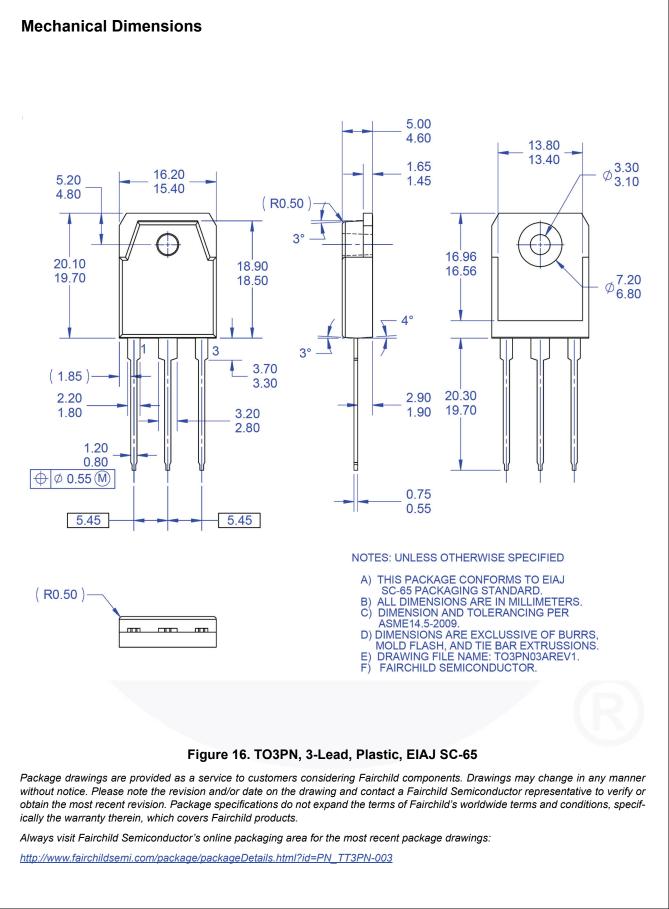
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